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APPLICANTS

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** CONTINUING DATA *****
None *D.H.K.*

** FOREIGN APPLICATIONS *****
 REPUBLIC OF KOREA 2003-35556 06/03/2003
yes D.H.K.

IF REQUIRED, FOREIGN FILING LICENSE GRANTED ** SMALL ENTITY **
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Foreign Priority claimed 35 USC 119 (a-d) conditions met Verified and Acknowledged	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance <i>[Signature]</i> <i>D.H.K.</i> Examiner's Signature Initials	STATE OR COUNTRY KOREA, REPUBLIC OF	SHEETS DRAWING 3	TOTAL CLAIMS 9	INDEPENDENT CLAIMS 2
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TITLE
 Field effect transistor using vanadium dioxide layer as channel material and method of manufacturing the field effect transistor

☐ All Fees